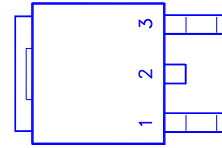
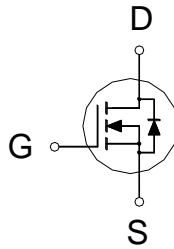




PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
700V	2.9Ω	4A



- 1. GATE
- 2. DRAIN
- 3. SOURCE

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	700	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current ²	T _C = 25 °C	I_D	4	A
	T _C = 100 °C		2.4	
Pulsed Drain Current ¹		I_{DM}	16	
Avalanche Current ³		I_{AS}	2	
Avalanche Energy ³		E_{AS}	20	mJ
Power Dissipation	T _C = 25 °C	P_D	78	W
	T _C = 100 °C		31	
Operating Junction & Storage Temperature Range		T _j , T _{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{θJC}$		1.6	°C / W
Junction-to-Ambient	$R_{θJA}$		62.5	

¹Pulse width limited by maximum junction temperature.

²Limited only by maximum temperature allowed

³V_{DD} = 50V, L = 10mH ,Starting T_J = 25°C

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

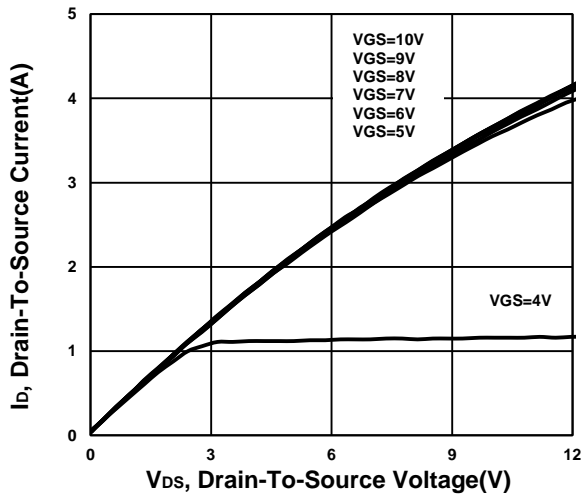
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	700			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 30V$			±100	nA
Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 700V, V_{GS} = 0V, T_C = 25\text{ °C}$			1	μA
		$V_{DS} = 560V, V_{GS} = 0V, T_C = 125\text{ °C}$			10	

Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 2A$		2.4	2.9	Ω
Forward Transconductance ¹	g_{fs}	$V_{DS} = 10V, I_D = 2A$		7.2		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		662		pF
Output Capacitance	C_{oss}			61		
Reverse Transfer Capacitance	C_{rss}			6		
Total Gate Charge ²	Q_g	$V_{DD} = 560V, I_D = 4A, V_{GS} = 10V$		15.6		nC
Gate-Source Charge ²	Q_{gs}			3.6		
Gate-Drain Charge ²	Q_{gd}			6		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DD} = 350V, I_D = 4A, R_G = 6\Omega$		36		nS
Rise Time ²	t_r			13.3		
Turn-Off Delay Time ²	$t_{d(off)}$			17		
Fall Time ²	t_f			12.2		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ C$)						
Continuous Current	I_S				4	A
Forward Voltage ¹	V_{SD}	$I_F = 4A, V_{GS} = 0V$			1	V
Reverse Recovery Time	t_{rr}	$I_F = 4A, di_F/dt = 100A / \mu S$		352		nS
Reverse Recovery Charge	Q_{rr}			2.4		uC

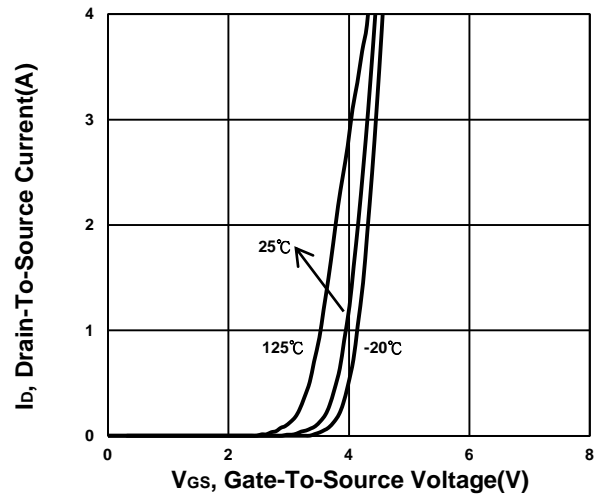
¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

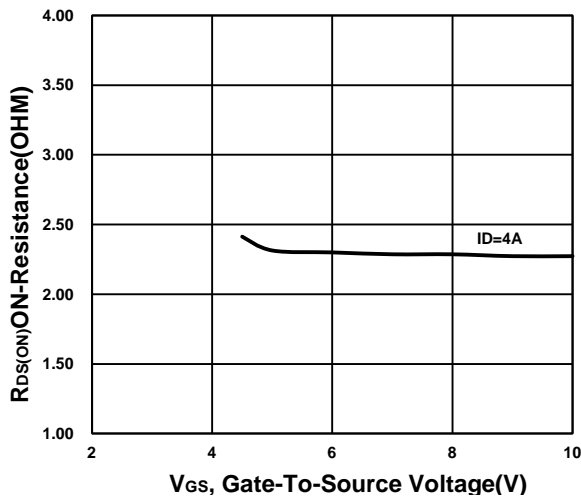
Output Characteristics



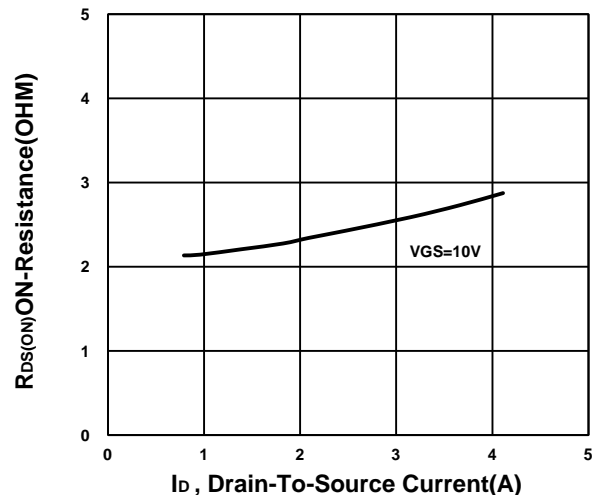
Transfer Characteristics



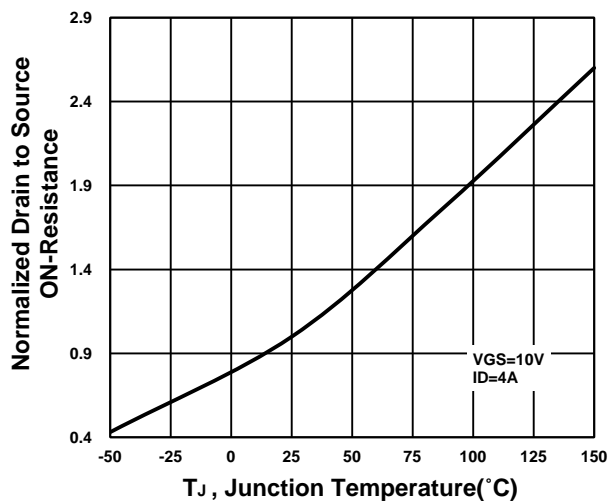
On-Resistance VS Gate-To-Source



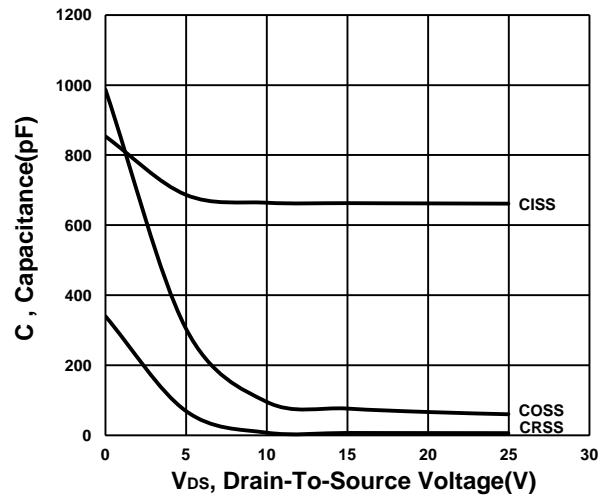
On-Resistance VS Drain Current



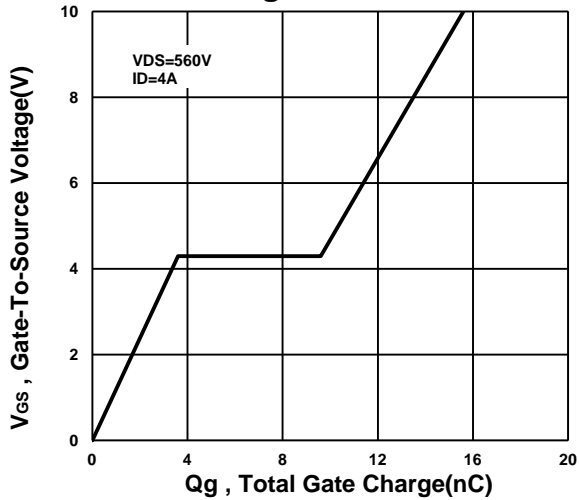
On-Resistance VS Temperature



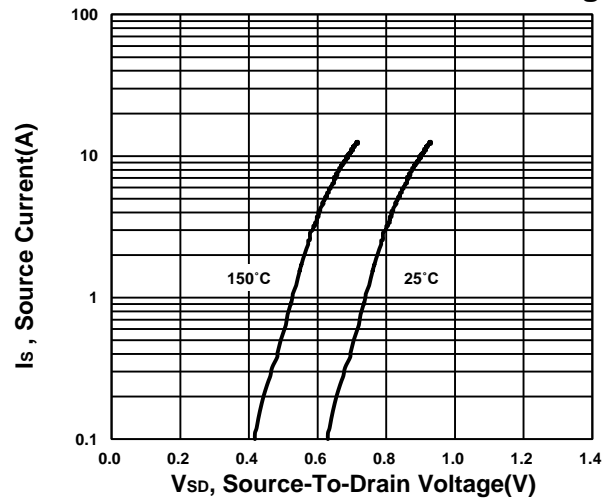
Capacitance Characteristic



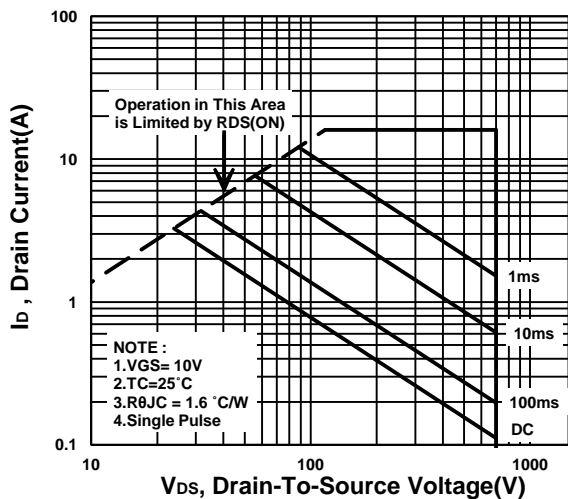
Gate charge Characteristics



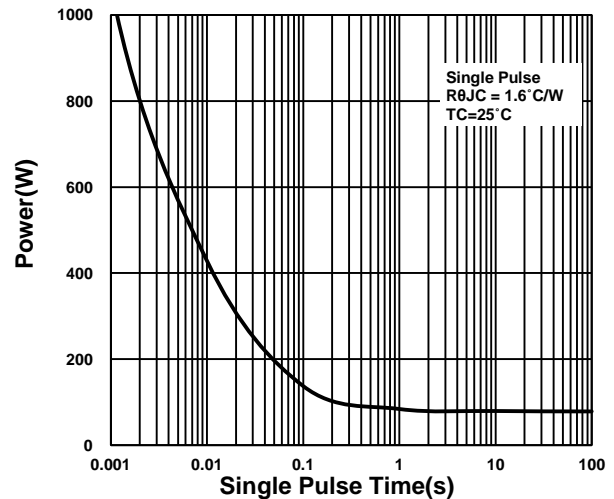
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

